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PTO/SB/08A (08-00)

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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>				<b>Complete if Known.</b>	
				Application Number	10/712,062
				Filing Date	November 14, 2003
				First Named Inventor	Shunpei YAMAZAKI et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham
				Attorney Docket Number	0756-7218
Sheet	1	of	1		

[illegible][illegible]

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Examiner Signature	<i>John A. [Signature]</i>		Date Considered <i>8/10/06</i>

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**U.S. PATENT DOCUMENTS**

Examiner Initials	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			

**FOREIGN PATENT DOCUMENTS**

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		Office Action dated August 3, 1998 for Application Serial No. 08/784,293.	
		Office Action dated February 11, 1999 for Application No. 08/784,293.	
		Office Action dated January 17, 2003 for Application No. 08/784,293.	
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		Number	Kind Code <sup>2</sup> (if known)			
JP		4,330,363		Biegesen et al.	05/18/1982	
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		5,089,441		Moslehi	02/18/1992	

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		EP	0 178 447			04/23/1986		Eng.

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		Kuper et al., "Effects of Fluorine Implantation on the Kinetics of Dry Oxidation of Silicon," Volume 60, No. 3, August 1, 1986, pp. 985-990, J. Applied Physics.	
		Nemanich et al., "Structure and Growth of the Interface of Pd on a-SiH," June 15, 1981, pp. 6828-6831, The American Physical Society Physics Review, Vol. 23, No. 12.	
		Wolf et al., "Thermal Oxidation of Single Crystal Silicon," Volume 1, 1986, pp. 207-211, Silicon Processing for the VLSI Era.	
		Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals," Volume 95, 1986, pp. 635-640, Akademikian Lavrentev Prospekt 13, 630090 Novosibirsk 90, USSR.	
		Hayzelden et al., "Silicide Formation and Silicide Mediated Crystallization of Nickel-Implanted Amorphous Silicon Thin Films," June 1, 1993, pp. 8279-8289, J. Appl. Phys. 73(12)	
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